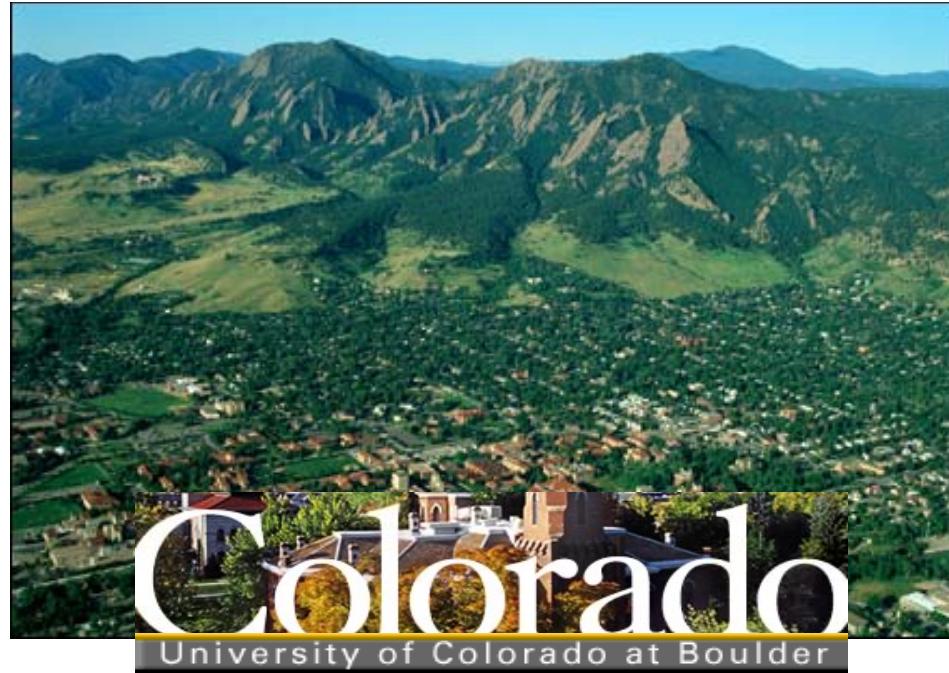
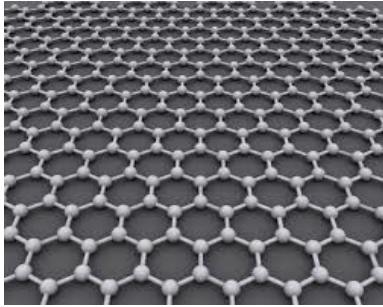


Disorder-driven quantum transition in semiconductors and Dirac semimetals



with: *S. Syzranov, V. Gurarie*

see: *PRL, PRB 2015*

\$: NSF, Simons Foundation

University of Utah, May 7, 2015

Outline

- Motivation
- Results
- Qualitative physics
- RG for ‘dirty’ semiconductors and Dirac semimetals
- Critical density of states and transport
- Lifshitz tails
- Conclusions

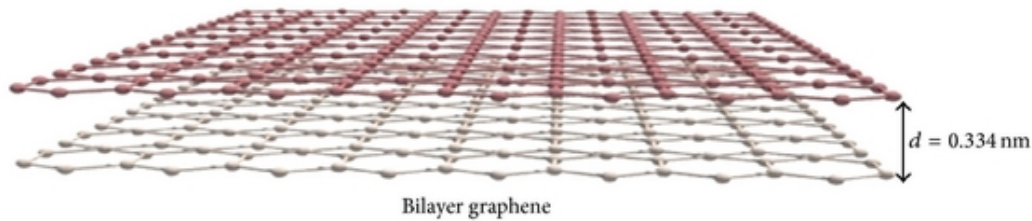
S. V. Syzranov, V. Gurarie, L. Radzihovsky, PRB 91, 035133 (2015)

S. V. Syzranov, L. Radzihovsky, V. Gurarie, PRL 114, 166601 (2015)

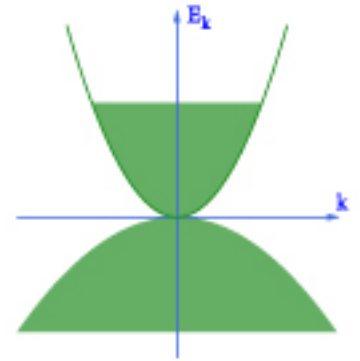
Motivation

Transport in lightly-doped ($E_F \ll W$) conductors

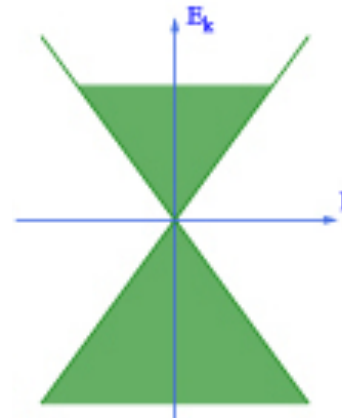
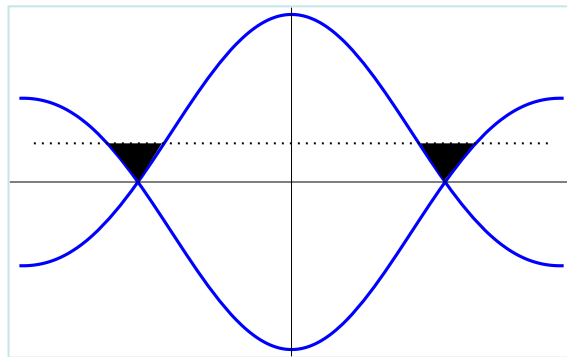
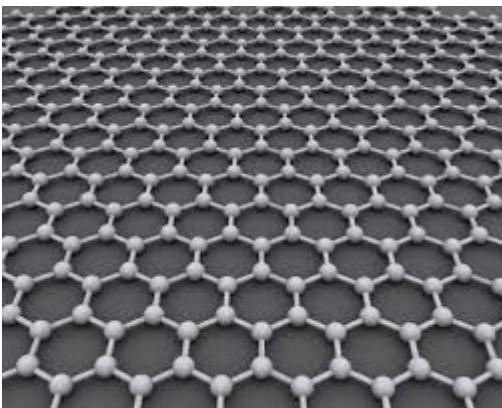
- *semiconductors, bilayer graphene:*



$$\epsilon_k \sim k^2$$



- *graphene, Weyl semimetals, topological insulators:*

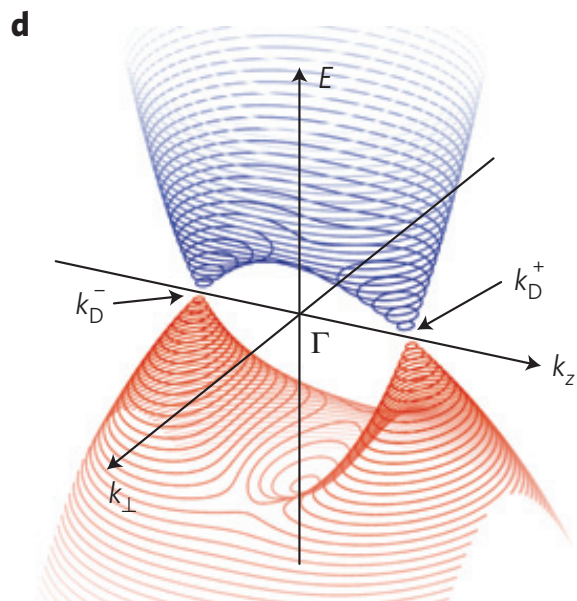


$$\epsilon_k \sim \sigma \cdot k$$



Landau quantization and quasiparticle interference in the three-dimensional Dirac semimetal Cd_3As_2

Sangjun Jeon^{1†}, Brian B. Zhou^{1†}, Andras Gyenis¹, Benjamin E. Feldman¹, Itamar Kimchi², Andrew C. Potter², Quinn D. Gibson³, Robert J. Cava³, Ashvin Vishwanath² and Ali Yazdani^{1*}



Results

study:

$$\varepsilon(\hat{\mathbf{p}})\psi + V(\mathbf{r})\psi = E\psi$$

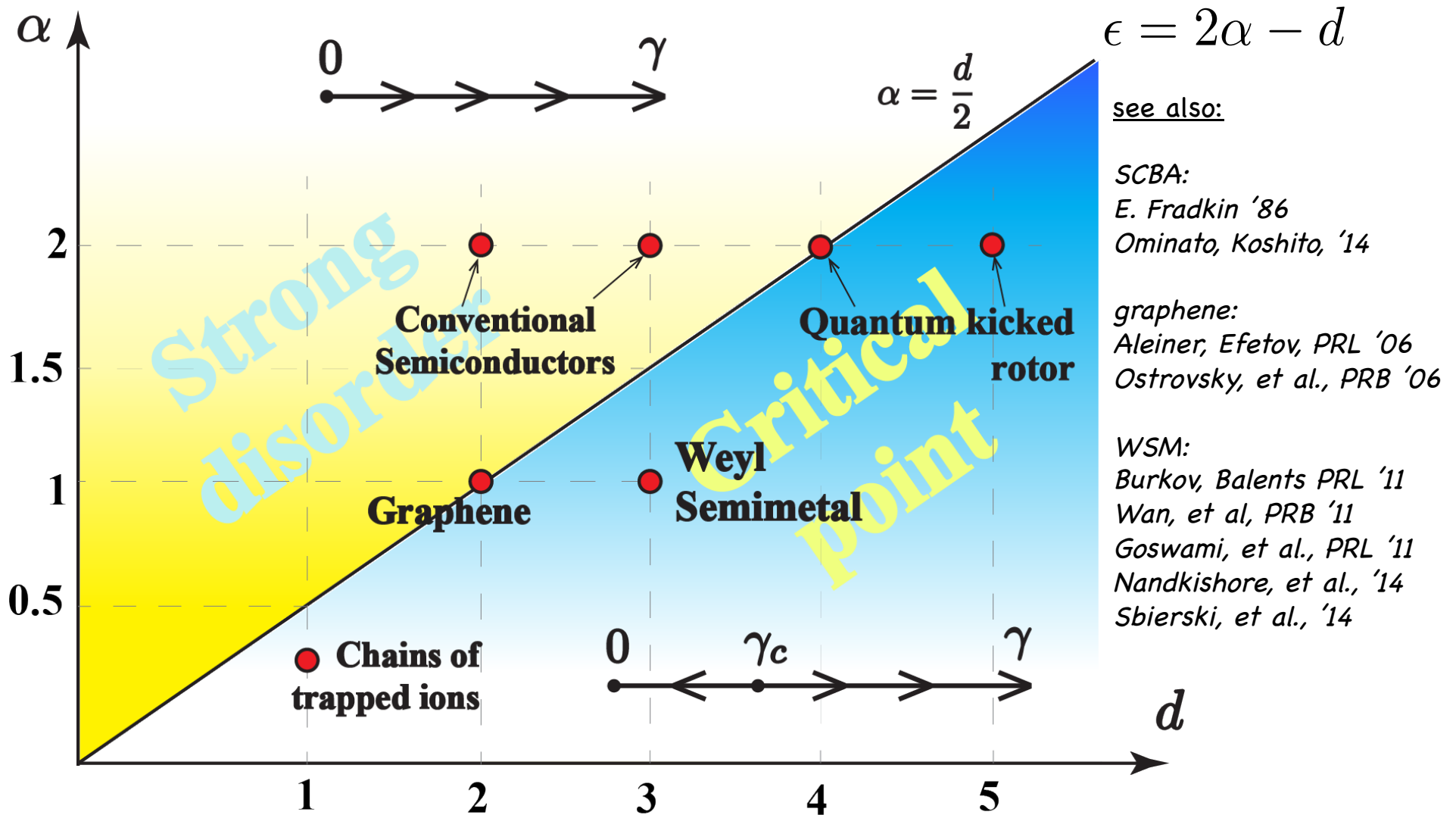
at bottom of the band, $E \rightarrow 0$

S. V. Syzranov, V. Gurarie, L. Radzihovsky, PRB 91, 035133 (2015)

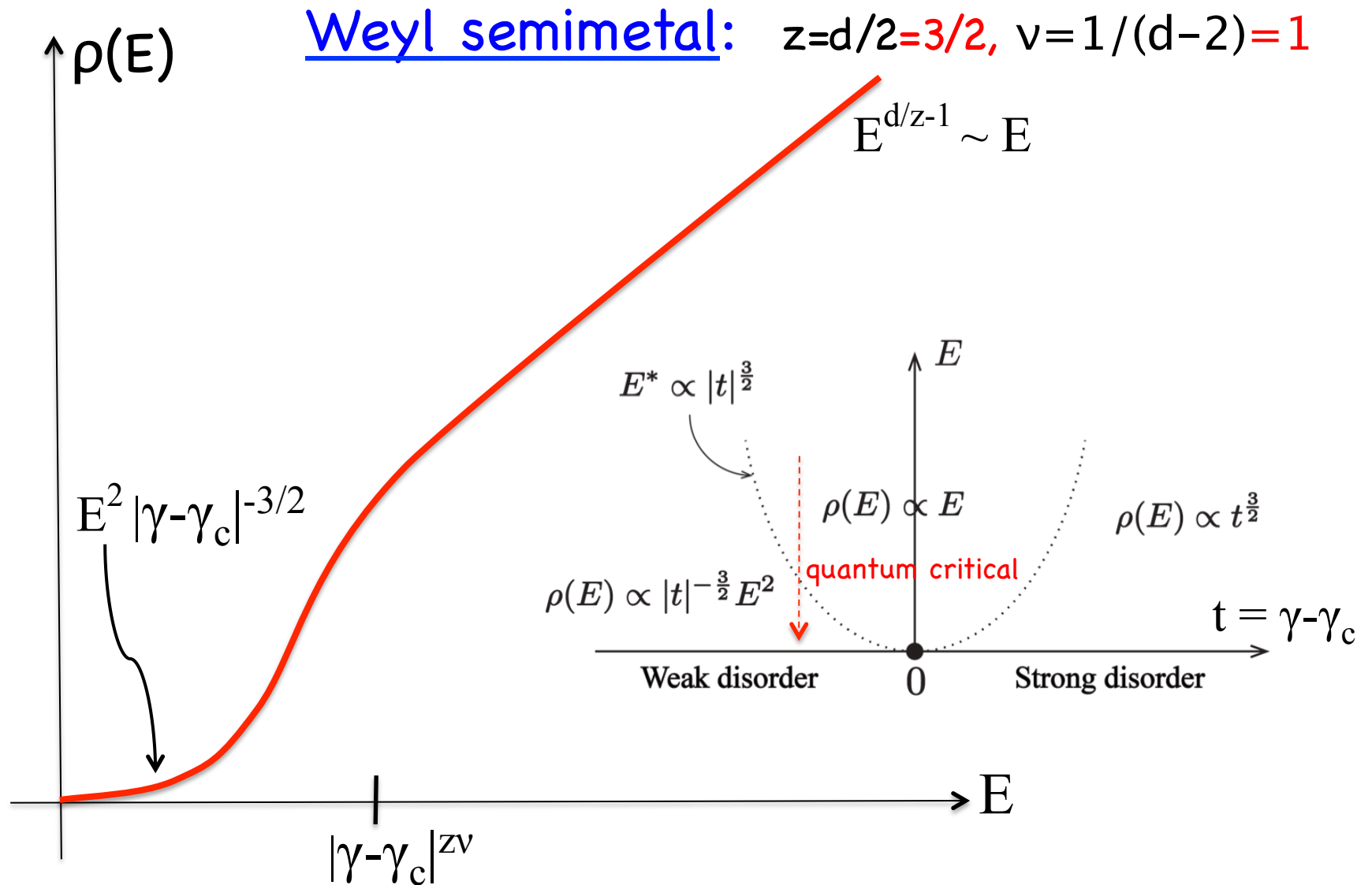
S. V. Syzranov, L. Radzihovsky, V. Gurarie, PRL 114, 166601 (2015)

results: “phase diagram”

non-interacting $\epsilon_k \sim k^\alpha$ in random potential



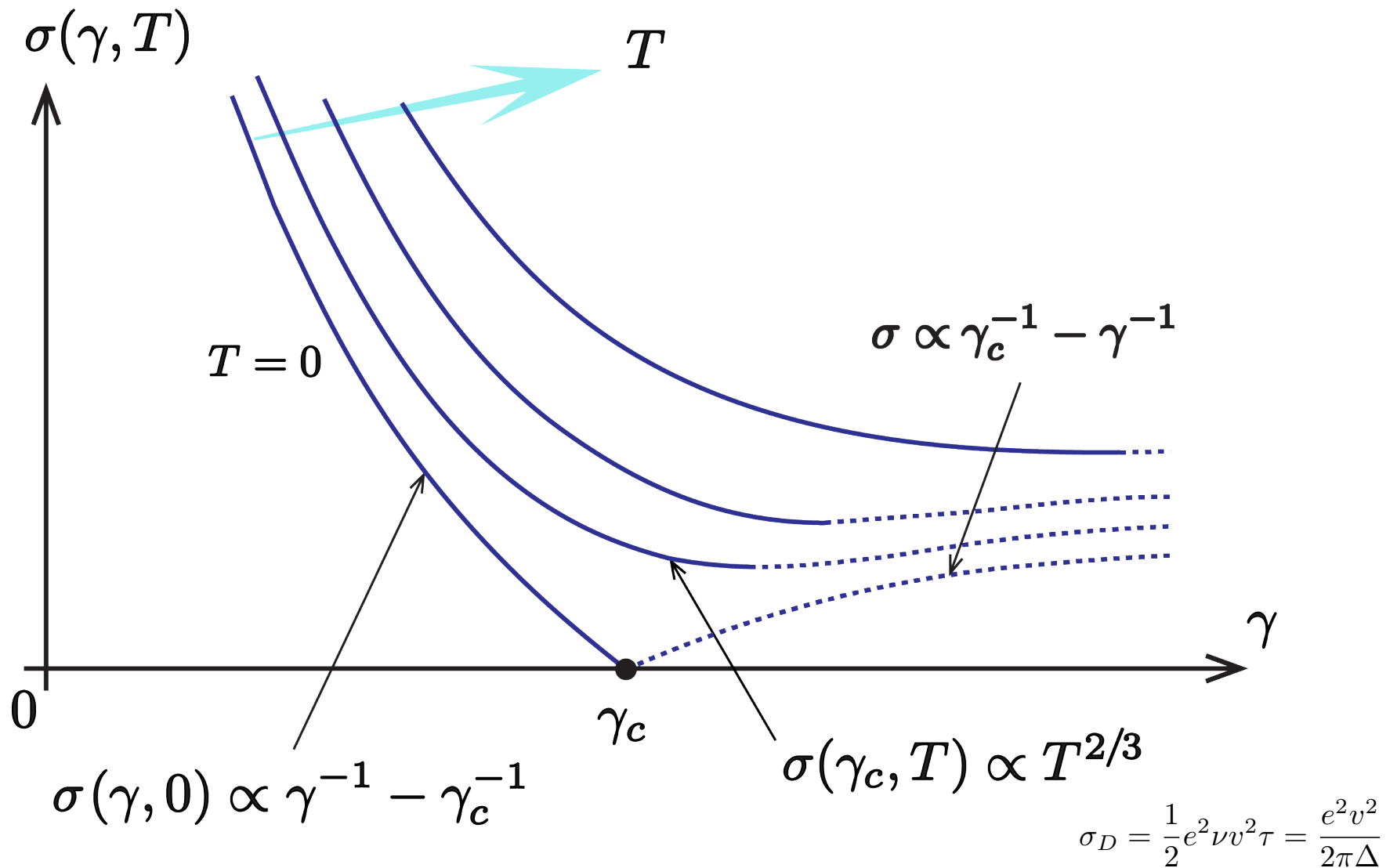
results: **critical density of states**



...ignoring rare regions of strong disorder Lifshitz tails

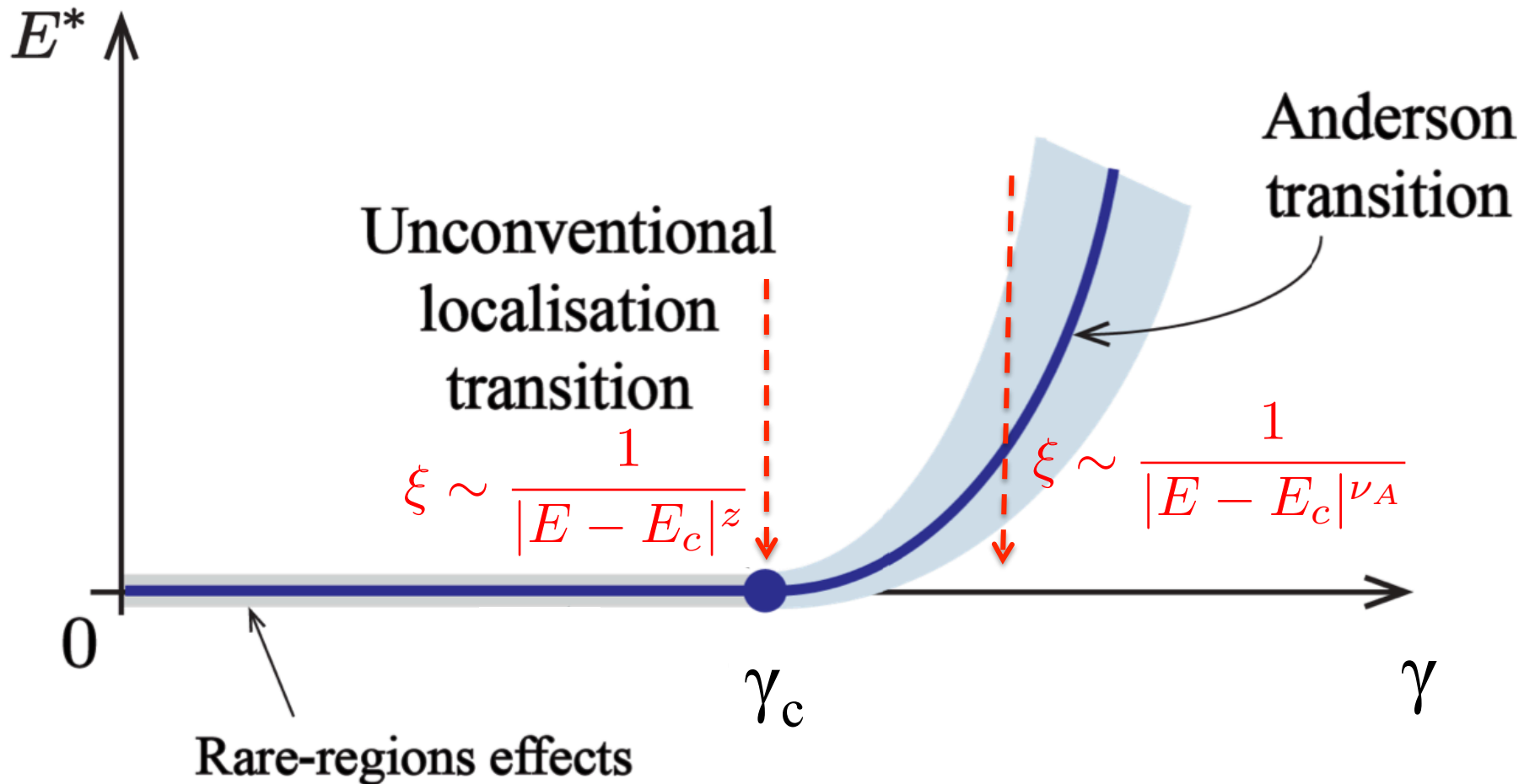
results: **critical conductivity**

Weyl semimetal: $z=d/2=3/2$, $\nu=1/(d-2)=1$



results: **nonanalytic mobility edge**

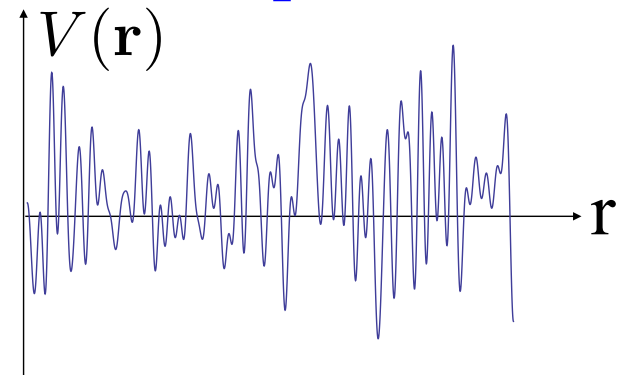
weakly-doped semiconductor



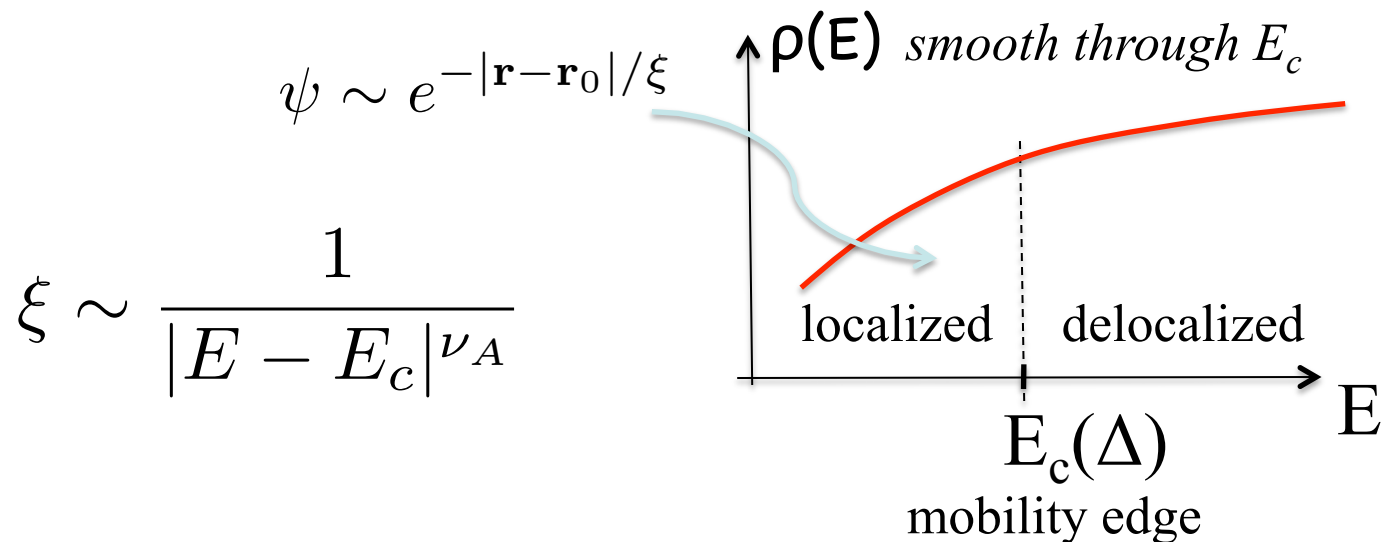
Anderson localization

- *noninteracting* quantum motion in a random potential

$$-\frac{\hbar^2}{2m}\nabla^2\psi + V(\mathbf{r})\psi = E\psi$$



- **conventional wisdom** (orthogonal)
 - $d < 2$: all states are localized
 - $d > 2$: localization-delocalization Anderson transition



Mobility edge E_c

Z. Phys. B – Condensed Matter 66, 21–30 (1987)

Localization, Quantum Interference, and the Metal-Insulator Transition

B. Bulka^{1*}, M. Schreiber², and B. Kramer¹

¹ Physikalisch-Technische Bundesanstalt, B

² Institut für Physik, Universität Dortmund,

Received September 10, 1986

mobility edge $E_c(\Delta)$ is a
smooth function of disorder
strength $\Delta \sim V_0^2$

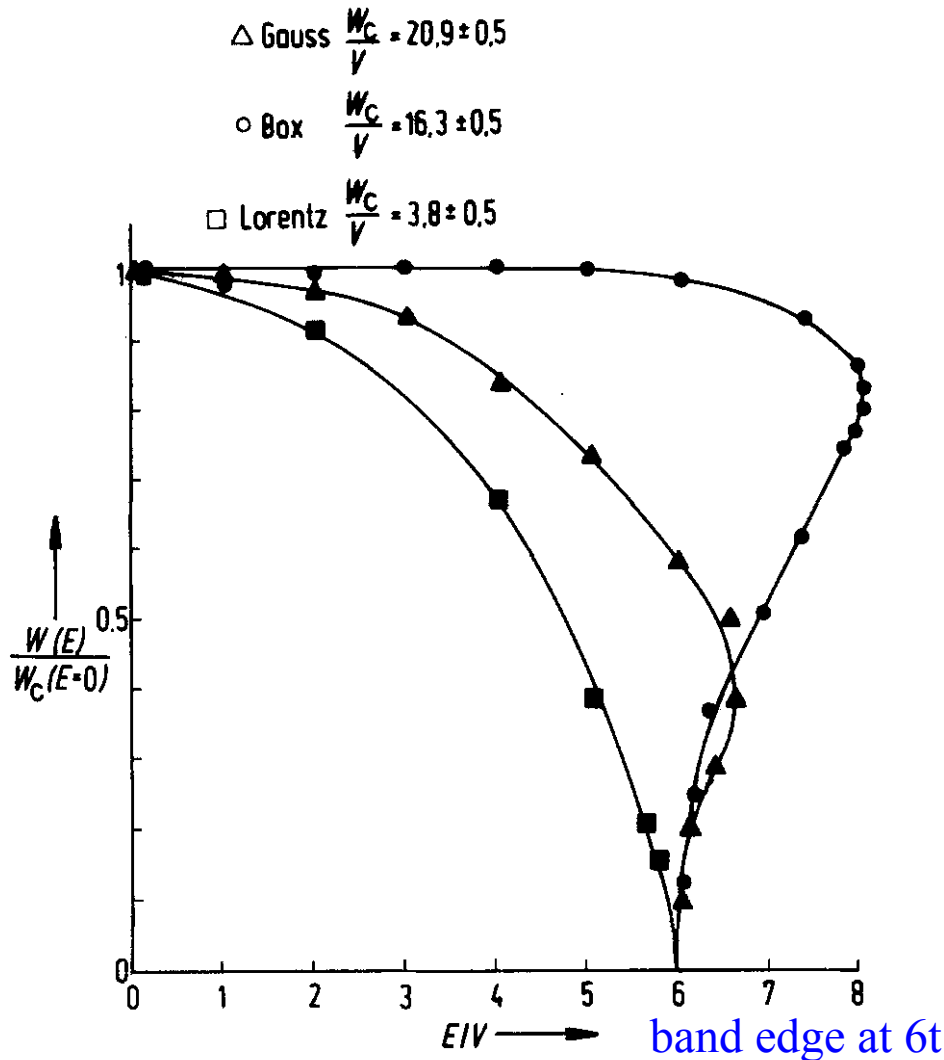


Fig. 1. Mobility edge trajectories $W_c(E)$ for the box (\bullet $W_c(0)/V = 16.3 \pm 0.5$), Gaussian (\blacktriangle $W_c(0)/V = 20.9 \pm 0.5$), and the Lorentzian (\blacksquare $W_c(0)/V = 3.8 \pm 0.5$) distribution

Model

low-density electrons in a random potential, $\mu \rightarrow 0$

$$\varepsilon(\hat{\mathbf{p}})\psi + V(\mathbf{r})\psi = E\psi \quad \rightarrow \quad Z \sim \int [d\psi] e^{iS}$$

$$S = \int_{\mathcal{C}} dt d^d r \bar{\psi} [\lambda i \partial_t - \varepsilon(\hat{\mathbf{p}}) - V(\mathbf{r})] \psi$$

$$\varepsilon(p) = \kappa p^\alpha \quad \overline{V(\mathbf{r})V(\mathbf{0})} = \Delta \delta^d(\mathbf{r})$$

$$\varepsilon(\hat{\mathbf{p}}) = \frac{\hat{p}^2}{2m}, \quad \text{semiconductor}$$

$$= v\sigma \cdot \hat{\mathbf{p}}, \quad \text{Weyl semimetal}$$

treat via *scaling, perturbation theory*, and *RG*
with $\varepsilon = (2\alpha - d)$ -expansion

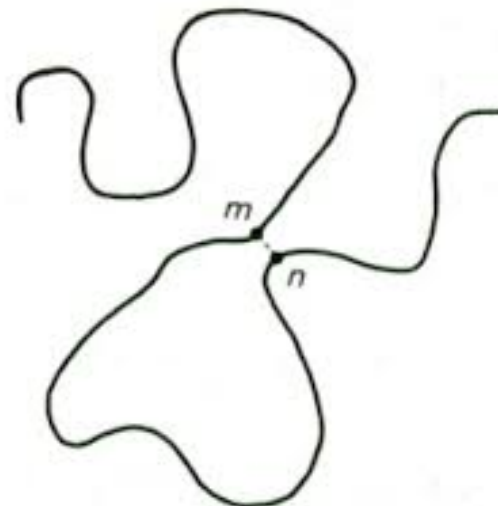
Related problems

- *Feynman's polaron coupled to a slow boson:*

- *world-line* \longrightarrow *self-avoiding polymer*

(deGennes '72)

$$H[r(t)] = \frac{1}{2} \int dt \left(\frac{d\mathbf{r}}{dt} \right)^2 + g \int dt \int dt' \delta^d(\mathbf{r}(t) - \mathbf{r}(t'))$$



- *singular corrections for $d < 4$ ($=2\alpha$, $\alpha=2$)*

- $R_G = (\langle r^2 \rangle)^{1/2} \sim L^\nu$, $\nu = 1/2 + O(4-d)$

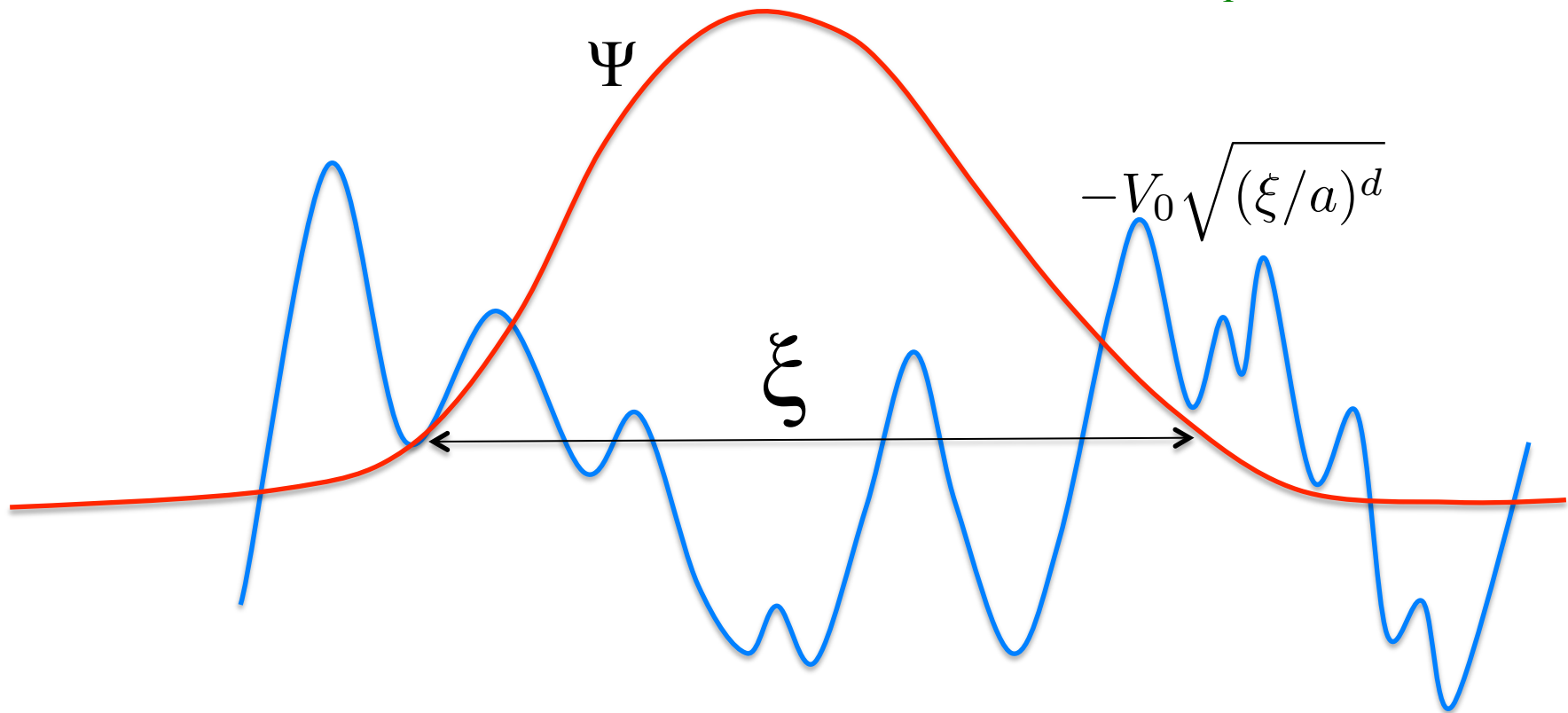
- *Interacting particles at low density (BCS-BEC):*

- *exact T-matrix* $\longrightarrow \frac{dg}{d\ell} = (2 - d)g - g^2$

The “Physics” via scaling

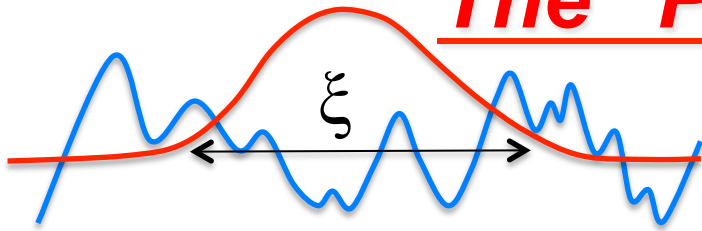
(distinct from interference effects near Fermi surface: e.g. weak localization)

*Fermi liquids are “protected” by Fermi sea, with $E_F \sim W$,
qualitatively different for low doping, with $E_F \ll W$*



bound-state formation in random potential $-V_0 \sqrt{(\xi/a)^d}$ on scale ξ

The "Physics" via scaling



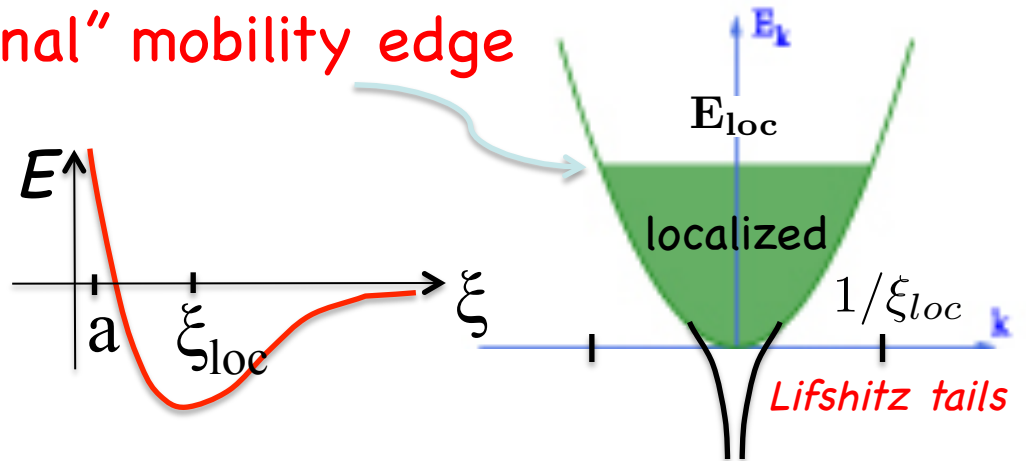
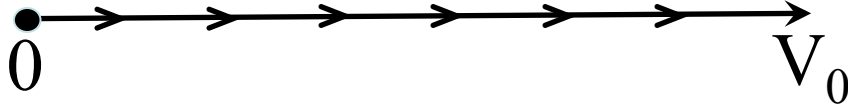
$V(r)$ averaged over wavelength $1/k \sim \xi$

$$E \sim \underbrace{\kappa \xi^{-\alpha}}_{E_K} - \underbrace{V_0 (\xi/a)^{-d/2}}_{V_{\text{eff}}}$$

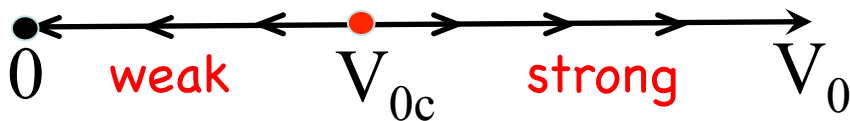
- $d < 2\alpha$: disorder dominates \rightarrow bound state for arbitrarily weak V_0

$$\xi_{\text{loc}} = a \left(\frac{\kappa}{V_0 a^\alpha} \right)^{\frac{2}{2\alpha-d}}$$

"conventional" mobility edge



- $d > 2\alpha$: weak disorder irrelevant below critical $V_{0c} = \kappa a^{-\alpha} = W$



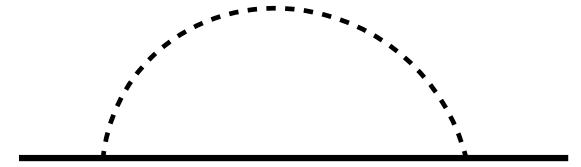
weak-to-strong disorder
quantum phase transition

Perturbation theory

$$S = \int_c dt d^d r \bar{\psi} [\lambda i \partial_t - \varepsilon(\hat{\mathbf{p}}) - V(\mathbf{r})] \psi$$

- scattering rate $1/\tau(E)$:

$$\Sigma(E) \sim \int d^d q \frac{1}{(E - q^\alpha) q^\alpha} \sim E^{d/\alpha - 1} \sim \frac{1}{\tau(E)}$$



$$\rightarrow G(E) \sim \frac{1}{E - k^\alpha - E^{d/\alpha - 1}}$$

usually
E-dependence
ignored at E_F

- Ioffe-Regel criterion $\gamma < 1$ vs $\gamma > 1$:

$$\gamma(E) \equiv \frac{\Sigma(E)}{E} \sim E^{d/\alpha - 2} \sim \frac{1}{k\ell(k)} \sim \frac{1}{kv(k)\tau(k)}$$

$d < 2\alpha$: (typical) disorder *dominates* at low E

$d > 2\alpha$: (typical) disorder is *irrelevant* at low E

$$\frac{\partial \gamma}{\partial \ell} = (2\alpha - d)\gamma + \dots$$

Perturbation theory

$$S = \int_c dt d^d r \bar{\psi} [\lambda i \partial_t - \varepsilon(\hat{\mathbf{p}}) - V(\mathbf{r})] \psi$$

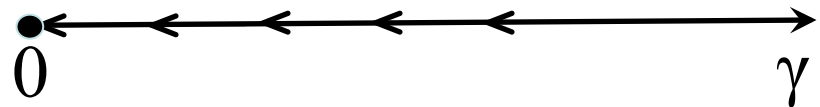
- Ioffe-Regel criterion, $\gamma < 1$ vs $\gamma > 1$:

$$\gamma(E) \equiv \frac{\Sigma(E)}{E} \sim E^{d/\alpha-2} \sim \frac{1}{k\ell(k)} \sim \frac{1}{kv(k)\tau(k)}$$

$d < 2\alpha$: (typical) disorder *dominates* at low E

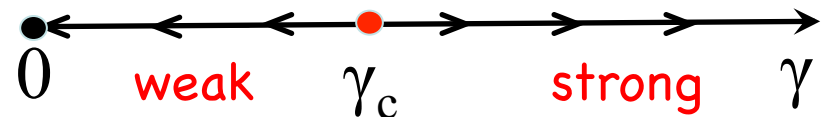
$d > 2\alpha$: (typical) disorder is *irrelevant* at low E (e.g., $d > 4$ *new physics*)

$$\frac{\partial \gamma}{\partial \ell} = (2\alpha - d)\gamma + \dots$$



What happens for stronger disorder for $d > 2\alpha$?

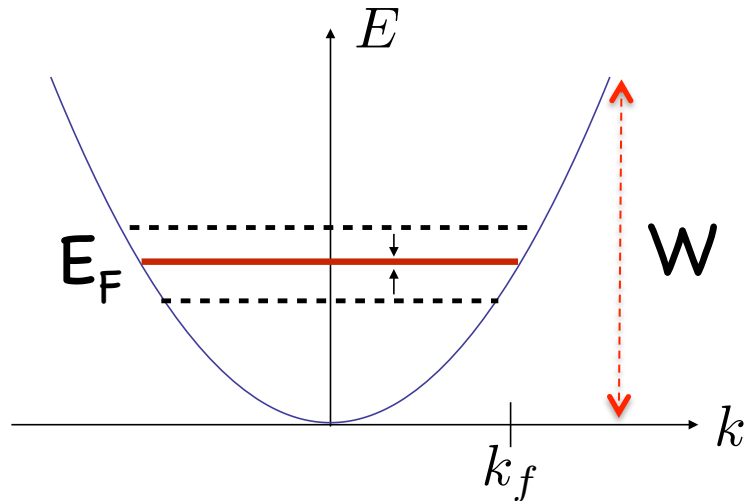
$$\frac{\partial \gamma}{\partial \ell} = (2\alpha - d)\gamma + c\gamma^2$$



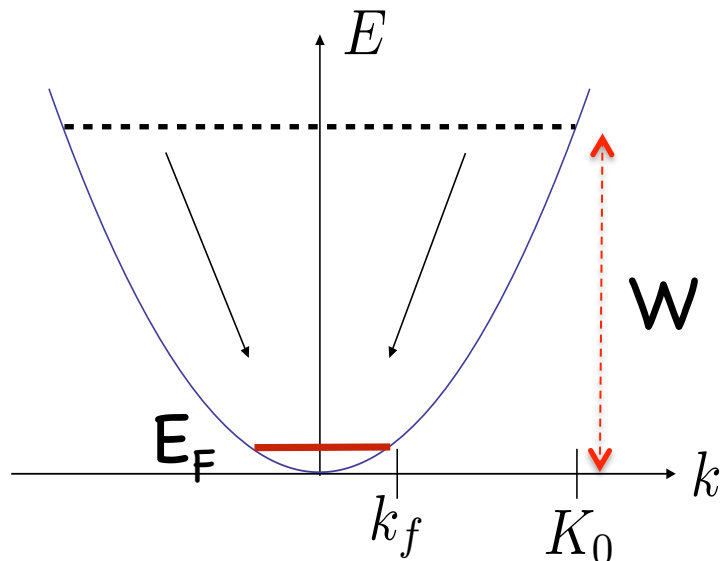
RG

$$S = \int_{\mathcal{C}} dt d^d r \bar{\psi} [\lambda i \partial_t - \varepsilon(\hat{\mathbf{p}}) - V(\mathbf{r})] \psi$$

- “conventional” (Shankar) RG at Fermi surface



- “vacuum” RG down to the bottom of the band



RG

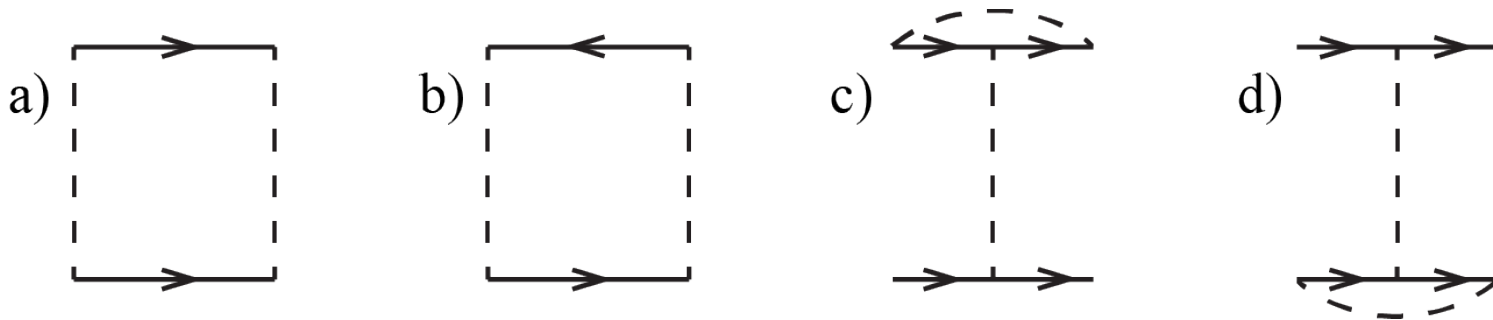
$$S = \int_C dt d^d r \bar{\psi} [\lambda i \partial_t - \varepsilon(\hat{\mathbf{p}}) - V(\mathbf{r})] \psi$$

- rescaling and tree-level RG flow: $r = r' b$, $t = t' b^z$

$$\lambda(b) = \lambda, \quad \kappa(b) = \kappa b^{z-\alpha}, \quad \Delta(b) = \Delta b^{2z-d}$$

$$\longrightarrow \gamma(b) = \frac{\Delta(b)}{\kappa(b)^2} = \gamma b^{2\alpha-d} \equiv \gamma e^{\epsilon \ell}$$

- momentum-shell RG flow: integrate out $K_0/b < k < K_0$

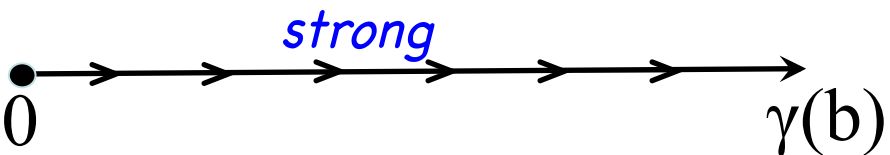


$$\frac{d\lambda}{d\ell} = \gamma\lambda, \quad \frac{d\gamma}{d\ell} = \epsilon\gamma + 2\alpha\gamma^2$$

Mobility threshold & transition

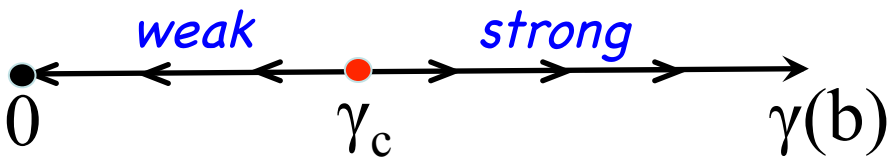
$$\gamma(b) = \frac{\gamma b^\epsilon}{1 - \gamma/\gamma_c + (\gamma/\gamma_c)b^\epsilon}, \quad \lambda(b) = \left[\frac{\gamma(b)}{\gamma} b^{-\epsilon} \right]^{1/2\alpha}, \quad \gamma_c = -\frac{\epsilon}{2\alpha}$$

renormalized Drude conductivity ($\gamma < 1$): $\sigma_D(b) = \frac{v(b)^2}{2\pi\gamma(b)b^{-\epsilon}}$

• $\epsilon > 0$ ($d < 2\alpha$): 

--> *disorder dominates for $k < K_{loc} = K_0 \left(1 + \frac{|\gamma_c|}{\gamma}\right)^{-1/\epsilon}$*

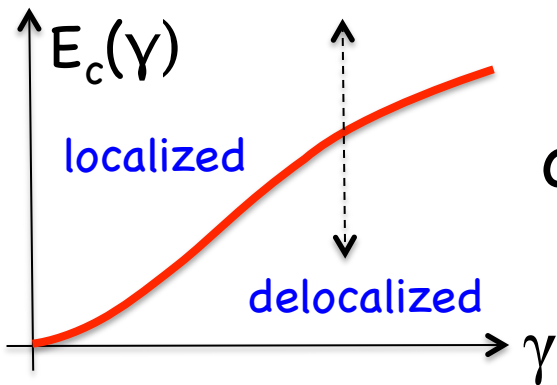
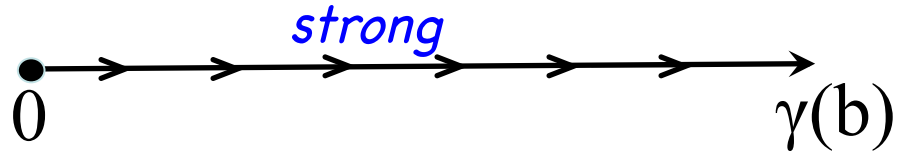
--> mobility threshold of Anderson transition

• $\epsilon < 0$ ($d > 2\alpha$): 

--> disorder-driven quantum transition $T=0, \mu \rightarrow 0$

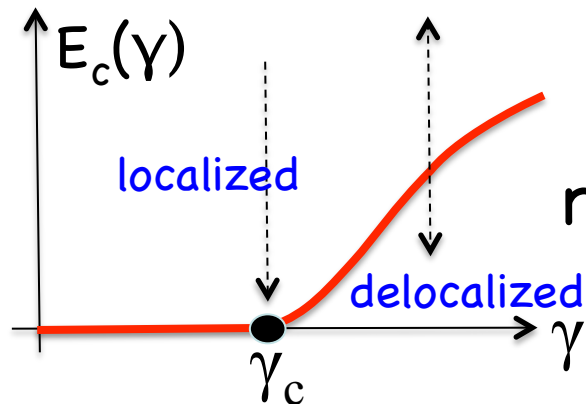
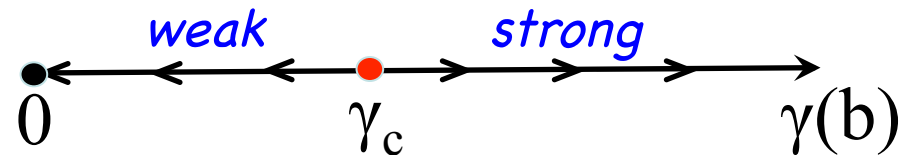
Mobility Edge

- $\epsilon > 0$ ($d < 2\alpha$):



conventional Anderson transition

- $\epsilon < 0$ ($d > 2\alpha$):



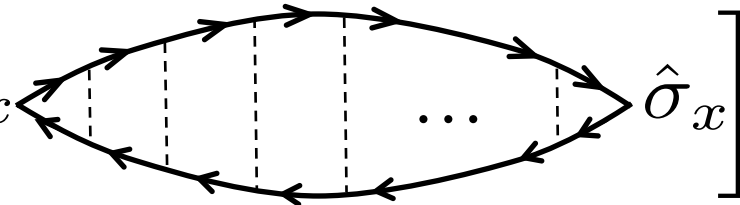
nonanalytic mobility edge

$$E_c(\gamma) \sim (\gamma - \gamma_c)^{z\nu}, \quad \gamma > \gamma_c$$

Conductivity

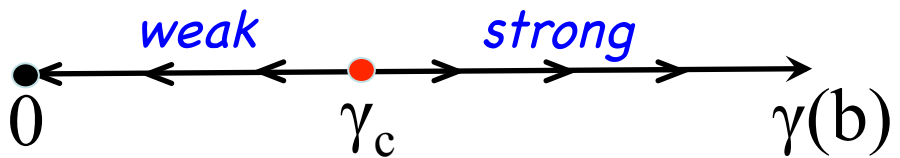
$$\sigma_{ij}(\omega) = \frac{e^2}{2\pi\omega} \int dE [n_F(E) - n_F(E + \omega)] \int d^d r' \overline{\text{Tr} \hat{v}_{i\mathbf{r}} G^A(E + \omega, \mathbf{r}, \mathbf{r}') \hat{v}_{j\mathbf{r}'} G^R(E, \mathbf{r}', \mathbf{r})}$$

Weyl semimetal:

$$\begin{aligned} \longrightarrow \sigma_{xx} &= \frac{e^2 v^2}{2\pi} \sum \text{Tr} \left[\hat{\sigma}_x \left(\text{Diagram} \right) \hat{\sigma}_x \right] \\ &= \frac{1}{2} e^2 v^2 \nu \tau = \frac{e^2 v^2}{2\pi \Delta} \end{aligned}$$


$$\begin{aligned} \longrightarrow \tau^{-1} &= -2 \text{Im} \Sigma_R = -2\Delta \int \frac{1}{\varepsilon - v \vec{\sigma} \cdot \vec{k} + \frac{i}{2\tau}} \\ &= \pi \nu \Delta \end{aligned}$$

Scaling theory of critical transport

- $\epsilon < 0$ ($d > 2\alpha$): 

$$\xi \sim |\gamma - \gamma_c|^{-\nu} \equiv |\delta\gamma|^{-\nu} \quad \sigma \sim \xi^{2-d}$$

$$\longrightarrow \sigma(\gamma, T, \mu) = |\delta\gamma|^{\nu(d-2)} g(T|\delta\gamma|^{-z\nu}, \mu/T)$$

$$\sigma(\gamma, 0, 0) \sim |\gamma - \gamma_c|^{\nu(d-2)} \quad \sigma(\gamma_c, T, 0) \sim T^{(d-2)/z}$$

- comparing with RG calculation, find (for 3d WSM):

$$\longrightarrow z = 3/2, \quad \nu = -1/(2\alpha-d) = 1$$

see also: Goswami, Chakravarty, PRL 107, 2011

$$(E \sim k^\alpha / \lambda(k) \sim k^{d/2})$$

Density of states

$$\begin{aligned}\rho(E) &= -\frac{1}{\pi} \text{Im} \int \frac{d^d r}{V} \overline{G_R(\mathbf{r}, \mathbf{r}, E)} \\ &= \lambda(K_E) \cdot \rho_{\text{clean}}[\lambda(K_E)E]\end{aligned}$$

where:

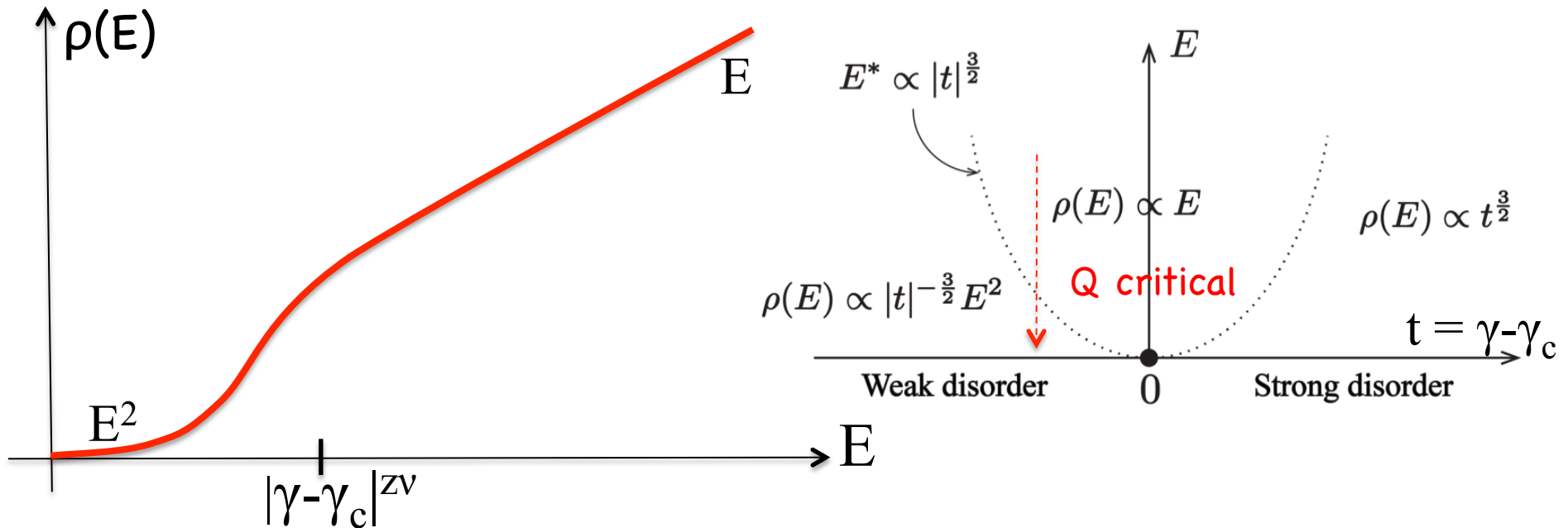
$$\gamma(b) = \frac{\gamma b^\epsilon}{1 - \gamma/\gamma_c + (\gamma/\gamma_c)b^\epsilon}, \quad \lambda(b) = \left[\frac{\gamma(b)}{\gamma} b^{-\epsilon} \right]^{1/2\alpha}$$

$$\lambda(K_E)E \sim \kappa K_E^\alpha$$

Scaling theory of density of states

$$\xi \sim |\gamma - \gamma_c|^{-\nu}, \quad E \sim \xi^{-z} \quad \text{WSM: } z=d/2=3/2, \quad \nu=1/(d-2)=1$$

$$\begin{aligned} \rho(E, \gamma) &\sim \frac{k^d \lambda_k}{\epsilon_k} \sim E^{d/z-1} f(E|\gamma - \gamma_c|^{-z\nu}) \\ &\sim E^2 |\gamma - \gamma_c|^{-3/2}, \quad \text{for } E \ll |\gamma - \gamma_c|^{z\nu} \\ &\sim E, \quad \text{for } E \gg |\gamma - \gamma_c|^{z\nu} \end{aligned}$$

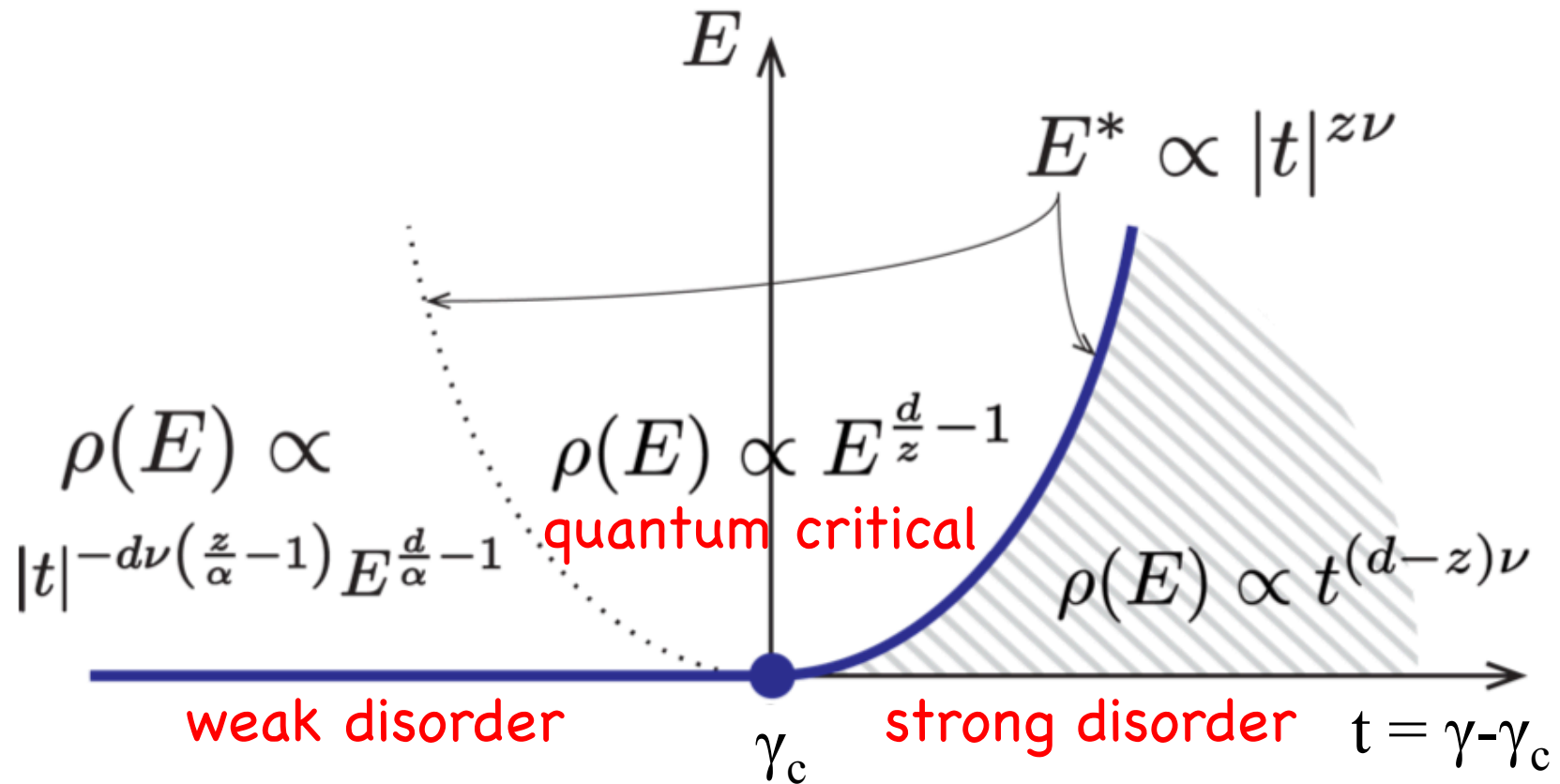


...ignoring rare regions of strong disorder Lifshitz tails (Nandkishore, et al.)

Scaling theory of density of states

$$\xi \sim |\gamma - \gamma_c|^{-\nu}, \quad E \sim \xi^{-z} \quad \text{semiconductor: } z=\alpha-\varepsilon/4, \nu=-1/\varepsilon$$

$$\rho(E, \gamma) \sim \frac{k^d \lambda_k}{\epsilon_k} \sim E^{d/z-1} f(E|\gamma - \gamma_c|^{-z\nu})$$



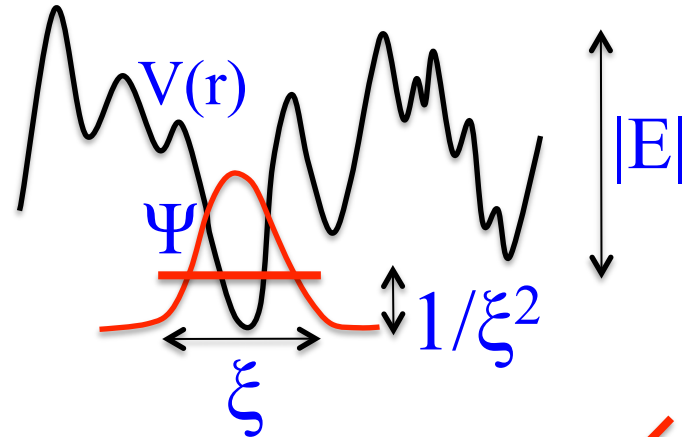
Lifshitz tails

- deeply lying states $E < 0$: $\varepsilon(\hat{\mathbf{p}})\psi + V(\mathbf{r})\psi = E\psi$

- probability of V , size ξ :

$$P(V) \sim e^{-\frac{1}{\Delta} \int d^d r V^2}$$

$$\sim e^{-\frac{\xi^d}{\Delta} (\kappa/\xi^\alpha + |E|)^2}$$



- maximize over ξ :

$d < 2\alpha$: $\xi \sim |E|^{-1/\alpha} \rightarrow \rho(E) \sim e^{-|E|^{(2\alpha-d)/\alpha}}$

Lifshitz tail

$d > 2\alpha$: $\xi \sim r_0 \rightarrow \rho(E) \sim e^{-\frac{r_0^{d-2\alpha}}{\gamma}}$

"our" tail

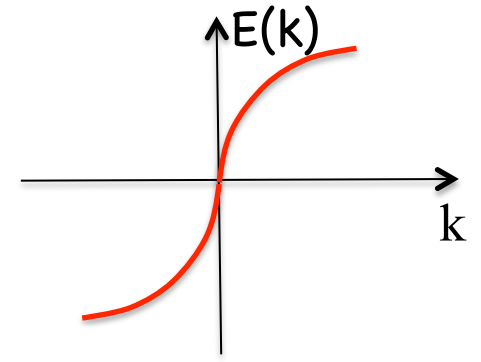
1d chiral model

M. Garttner, et al. 2015

- model: $\hat{h} = |\hat{p}|^\alpha \text{sgn}(\hat{p}) + V(x)$

-> long-range hopping $J_{xx'}$

$$\hat{H} = \sum_{x,x'} J_{xx'} \hat{a}_x^\dagger \hat{a}_{x'} + \sum_x V_x \hat{a}_x^\dagger \hat{a}_x$$



- high-d transition in 1d: $\alpha < \alpha_c = d/2 = 1/2$
 - $z = 1/2$
 - $v = 1/(1-2\alpha)$
 - $\rho(E) \sim E^\theta$
 - $\theta = d/z - 1 = 1$, for $\gamma = \gamma_c$
 - $\theta = d/\alpha - 1$, for $\gamma < \gamma_c$

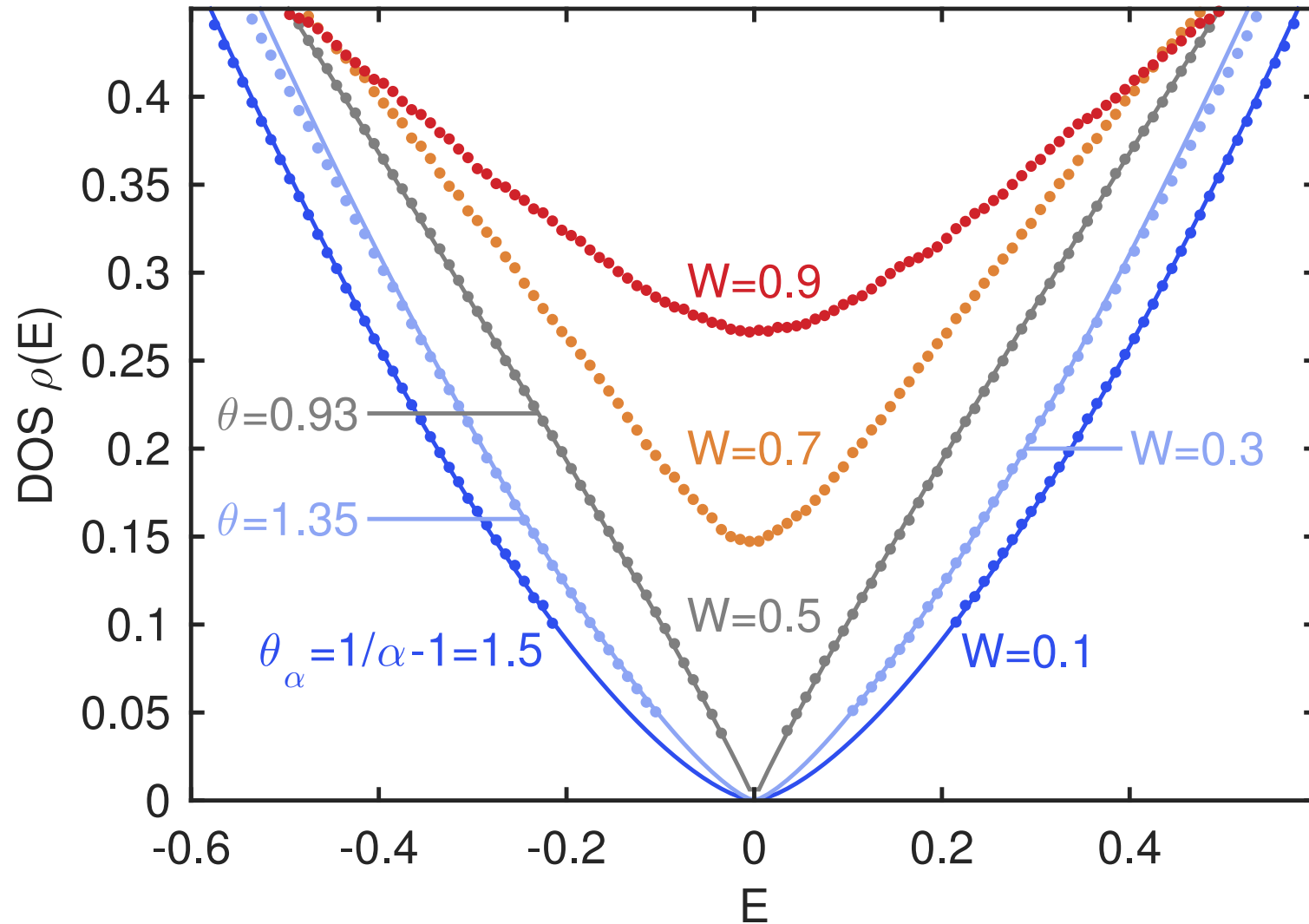
1d chiral model

M. Garttner, et al. 2015

Density of states $\rho(E) \sim E^\theta$

$\theta = d/z - 1 = 1$, for $\gamma = \gamma_c$

$\theta = d/\alpha - 1$, for $\gamma < \gamma_c$

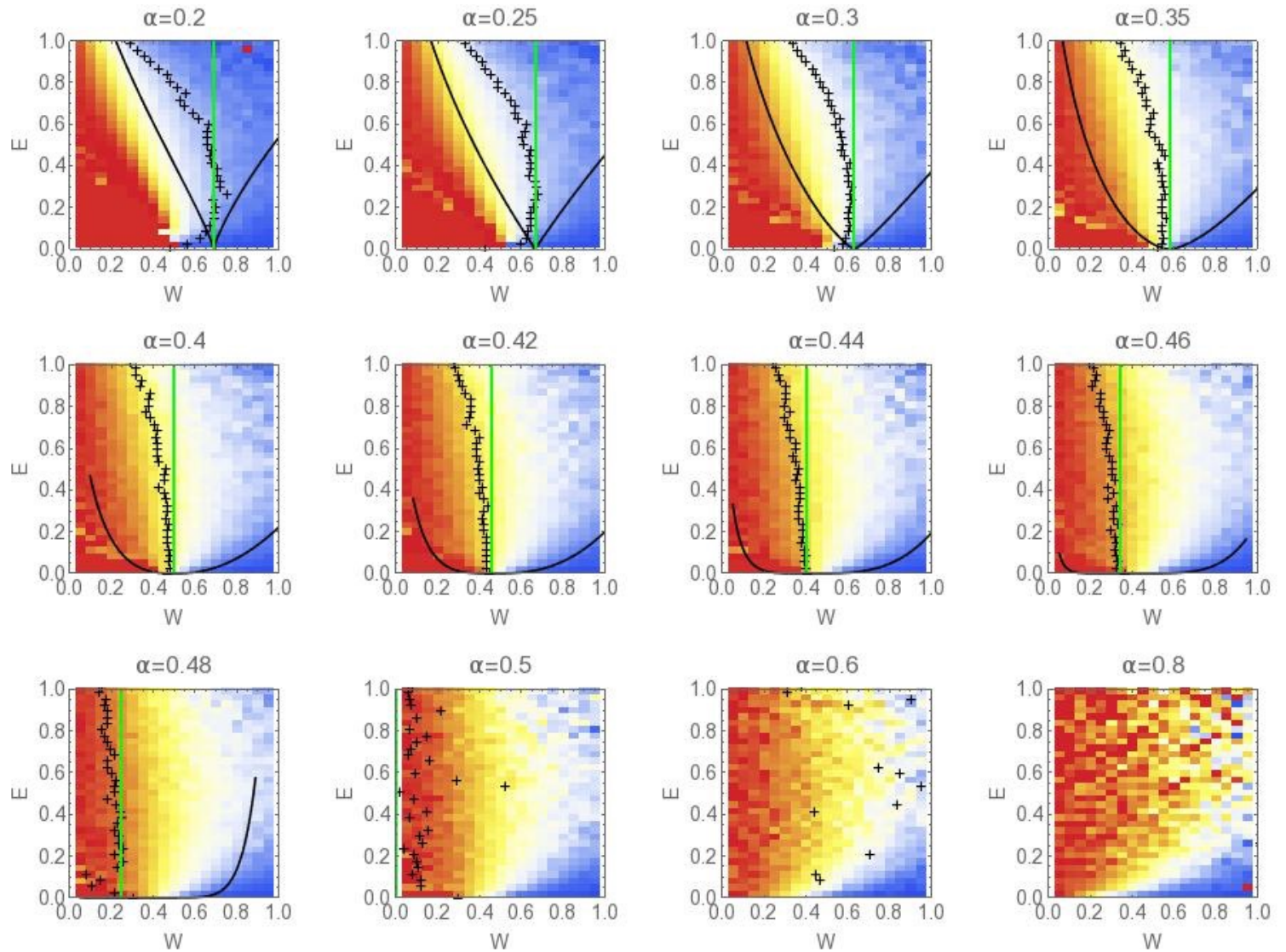


1d chiral model

M. Garttner, et al. 2015

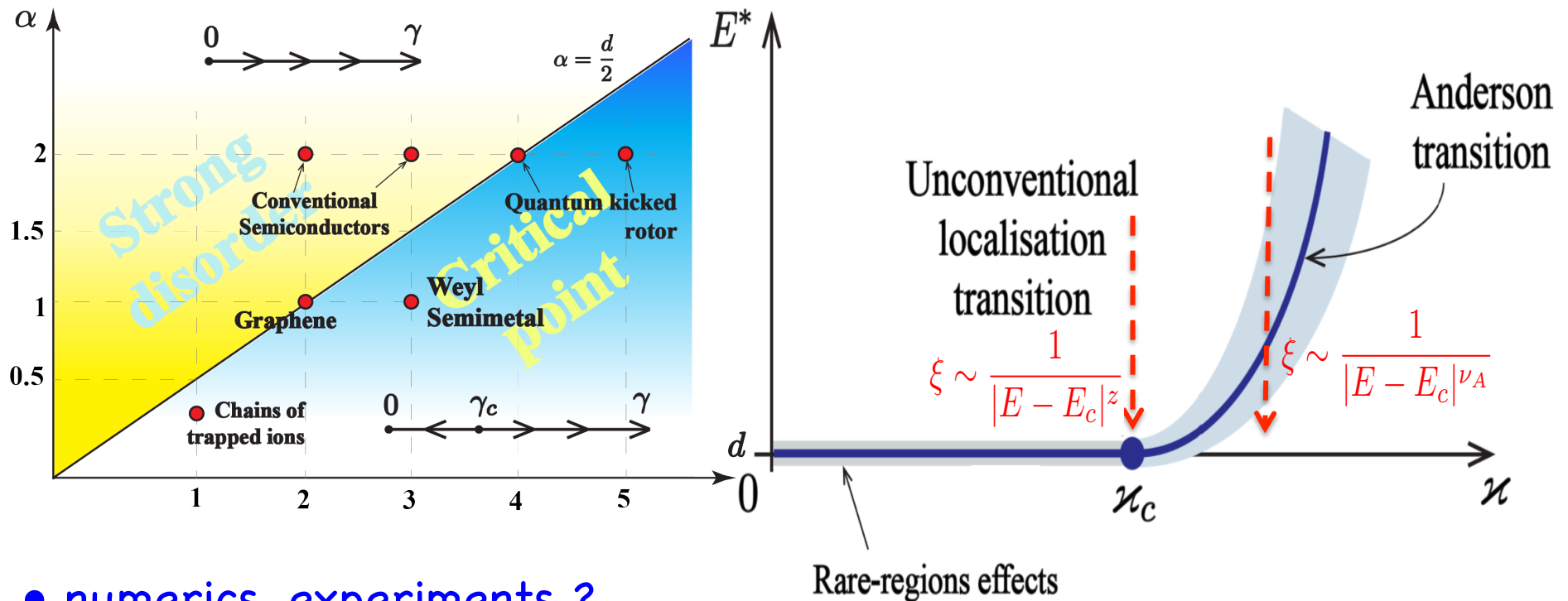
Density of states: $\rho(E) \sim E^\theta$

θ

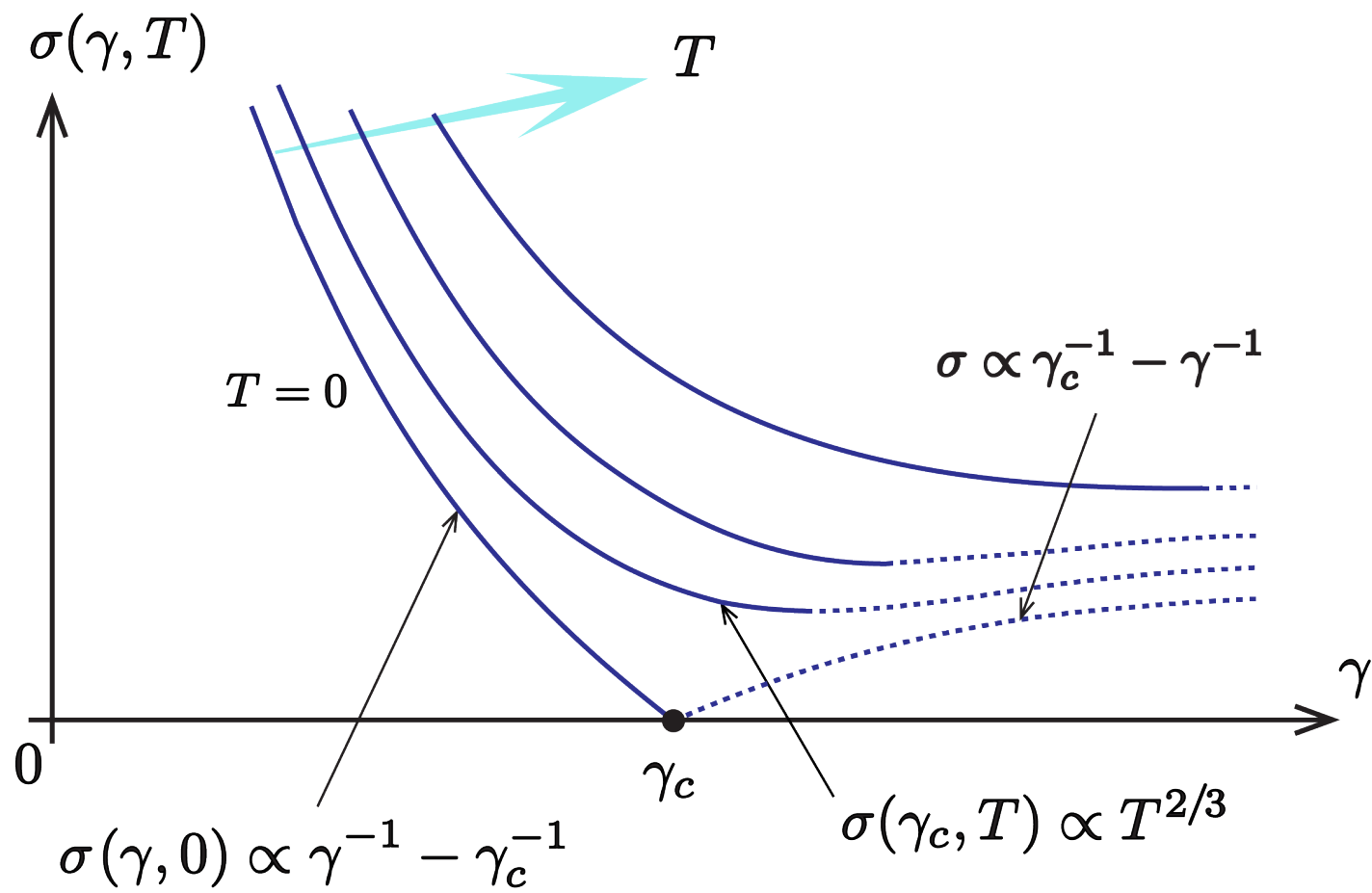


Summary and open questions

- studied transport in lightly-doped semiconductors, semimetals
- new weak-to-strong disorder-driven quantum phase transition
- RG and scaling theory --> conductivity, density of states



- numerics, experiments ?
- role of rare regions near critical point ?
- interplay with conventional Anderson localization ?
- Coulomb impurities ?



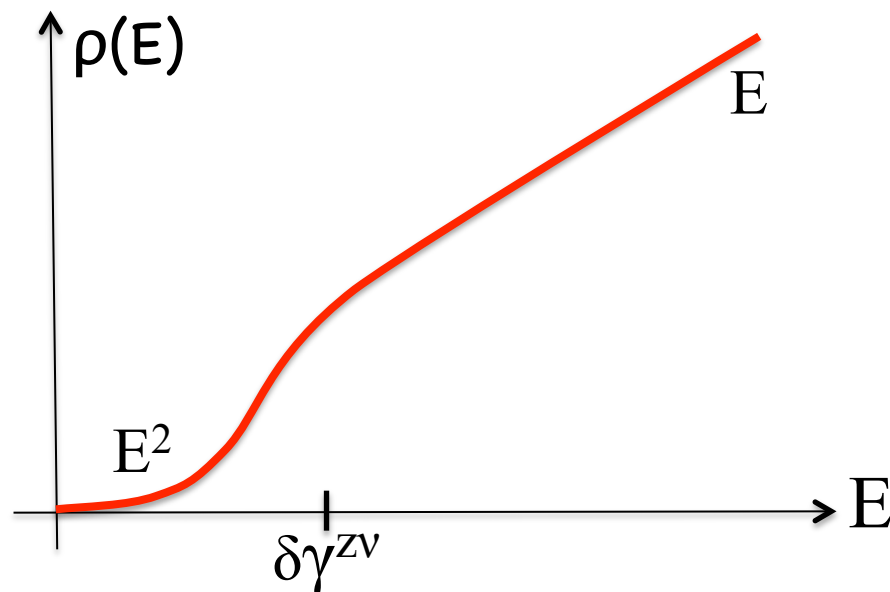
Results: critical density of states

$$\xi \sim |\gamma - \gamma_c|^{-\nu}, \quad \omega \sim \xi^{-z} \quad \text{WSM: } z=d/2=3/2 \\ \nu=1/(d-2)=1$$

$$\rho(\omega, \gamma) = \omega^{d/z-1} f(\omega |\delta\gamma|^{-z\nu})$$

$$\sim \omega^2 |\gamma - \gamma_c|^{-3/2}, \quad \text{for } \omega \ll |\delta\gamma|^{z\nu}$$

$$\sim \omega, \quad \text{for } \omega \gg |\delta\gamma|^{z\nu}$$



...ignoring rare regions of strong disorder Lifshitz tails (Nandkishore, et al.)

Results: critical conductivity of Weyl SM

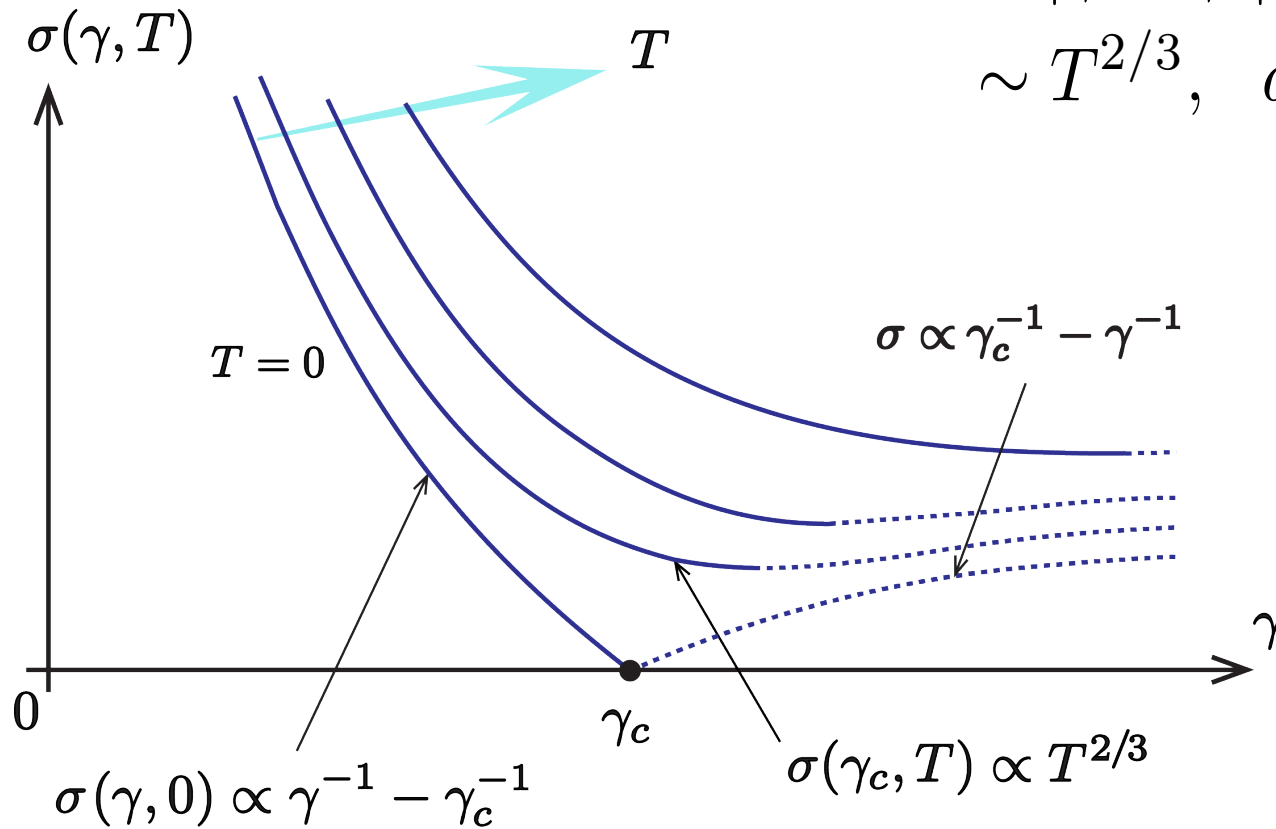
$$\xi \sim |\gamma - \gamma_c|^{-\nu}, \quad \omega \sim \xi^{-z}$$

WSM: $z=d/2=3/2$
 $\nu=1/(d-2)=1$

$$\sigma(\delta\gamma, T) \sim |\delta\gamma|^{\nu(d-2)} g [T|\delta\gamma|^{-z\nu}, \mu|\delta\gamma|^{-z\nu}]$$

$$\sim |\gamma - \gamma_c|, \quad \text{at } T = 0$$

$$\sim T^{2/3}, \quad \text{at } \gamma = \gamma_c$$



$$\sigma_D = \frac{1}{2} e^2 \nu v^2 \tau = \frac{e^2 v^2}{2\pi \Delta}$$

